

Amendments to the Claims

1. (Currently Amended) A multiple semiconductor chip (multi-chip) module, comprising at least a power semiconductor chip and a control semiconductor chip each mounted directly on an electrically conductive heat sink, wherein said power semiconductor chip comprises a Silicon-On-Insulator (SOI) device comprising a semiconductor substrate mounted directly on said electrically conductive heat sink, an insulating layer on said semiconductor substrate, an SOI layer on said buried insulating layer, and at least one semiconductor device provided in said SOI layer, wherein each semiconductor device in said SOI layer is electrically insulated from said electrically conductive heat sink by said insulating layer, and wherein said control semiconductor chip comprises a bulk technology semiconductor device having no insulating layer between a device layer and a substrate thereof, and having said substrate connected to ground potential and mounted directly on said electrically conductive heat sink, and said power semiconductor chip and said control semiconductor chip are directly mounted on said electrically conductive heat sink without the use of a separate electrical insulation layer.
2. (Original) A multi-chip module as in claim 1, wherein said control semiconductor chip semiconductor device comprises a BIMOS device.
3. (Original) A multi-chip module as in claim 1, wherein said control semiconductor chip semiconductor device comprises a CMOS device.

4. (Original) A multi-chip module as in claim 1, wherein said control semiconductor chip semiconductor device comprises a bipolar device.
5. (Original) A multi-chip module as in claim 1, wherein said conductive heat sink is connected to ground potential.
6. (Original) A multi-chip module as in claim 1, wherein said conductive heat sink comprises a metal.
7. (Original) A multi-chip module as in claim 6, wherein said metal comprises copper.
8. (Cancelled).